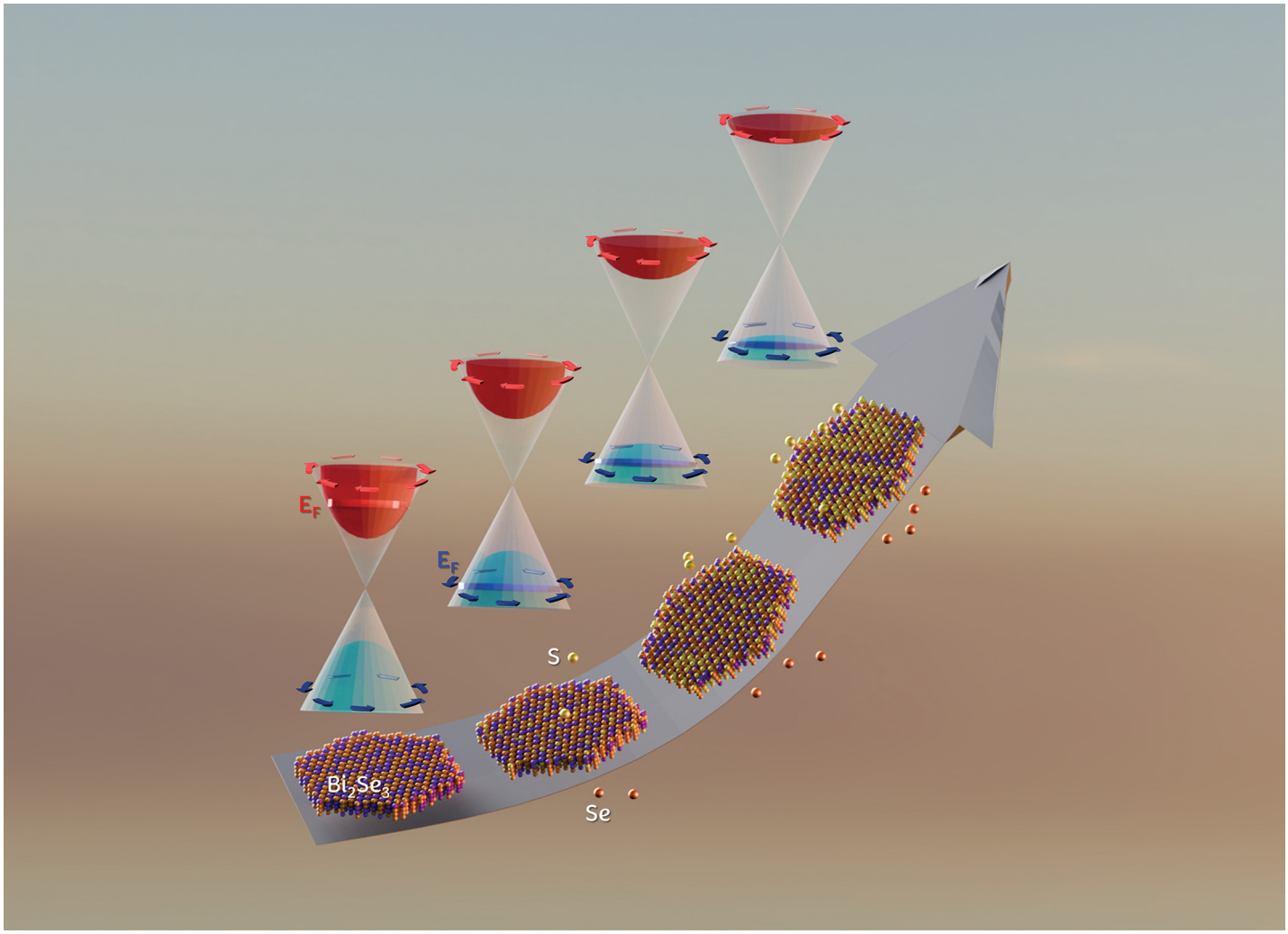
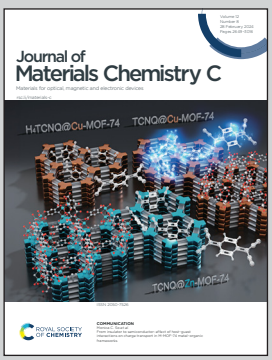


Showing collaborative research from Bar-Ilan University, Israel, National Technical University of Athens, Greece, Tel Aviv University, Israel, University of Massachusetts, USA, and Graphenea, Spain.

From monolayer to thin films: engineered bandgap in CVD grown $Bi_2Se_{(3-x)}S_x$ topological insulator alloys

Using chemical vapor deposition (CVD), the scalable growth of topological insulator alloys $Bi_2Se_{(3-x)}S_x$ with composition-tunable bandgap and free from surface-state pinning was achieved. This research paves the way for the controlled growth of topological insulators, suitable for quantum optoelectronics and spintronics applications.

As featured in:



See Doron Naveh *et al.*, *J. Mater. Chem. C*, 2024, **12**, 2723.

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